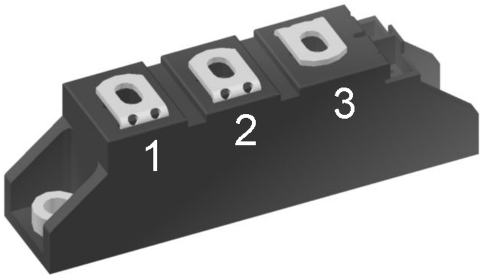
Standard Rectifier Module

V_{RRM} = 2x 1600 V
I_{FAV} = 85 A
V_F = 1.1 V

Phase leg

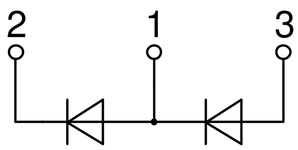
Part number

MDMA85P1600TG



Backside: isolated

E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

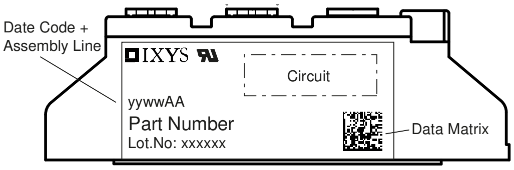
- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1700	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1600	V
I_R	*reverse current*	V_R = 1600 V	T_{VJ} = 25°C			100	µA
		V_R = 1600 V	T_{VJ} = 150°C			2	mA
V_F	*forward voltage drop*	I_F = 85 A	T_{VJ} = 25°C			1.15	V
		I_F = 170 A				1.38	V
		I_F = 85 A	T_{VJ} = 125°C			1.10	V
		I_F = 170 A				1.39	V
I_{FAV}	*average forward current*	T_C = 100°C rectangular d = 0.5	T_{VJ} = 150°C			85	A
V_{F0}	*threshold voltage*	*for power loss calculation only*	T_{VJ} = 150°C			0.79	V
r_F	*slope resistance*					3.5	mΩ
R_{thJC}	*thermal resistance junction to case*					0.35	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.20		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			350	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.50	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.62	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			1.28	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.38	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			11.3	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			10.9	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			8.13	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			7.87	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		60		pF

Package TO-240AA				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal				200	A
T_{VJ}	*virtual junction temperature*			-40		150	°C
T_{op}	*operation temperature*			-40		125	°C
T_{stg}	*storage temperature*			-40		125	°C
Weight					76		g
M_D	*mounting torque*			2.5		4	Nm
M_T	*terminal torque*			2.5		4	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*	*terminal to terminal*	13.0	9.7			mm
$d_{Spb/Apb}$		*terminal to backside*	16.0	16.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	4800			V
		t = 1 minute		4000			V



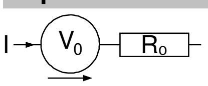
Part description

M = Module
D = Diode
M = Standard Rectifier
A = (up to 1800V)
85 = Current Rating [A]
P = Phase leg
1600 = Reverse Voltage [V]
TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA85P1600TG	MDMA85P1600TG	Box	36	513008

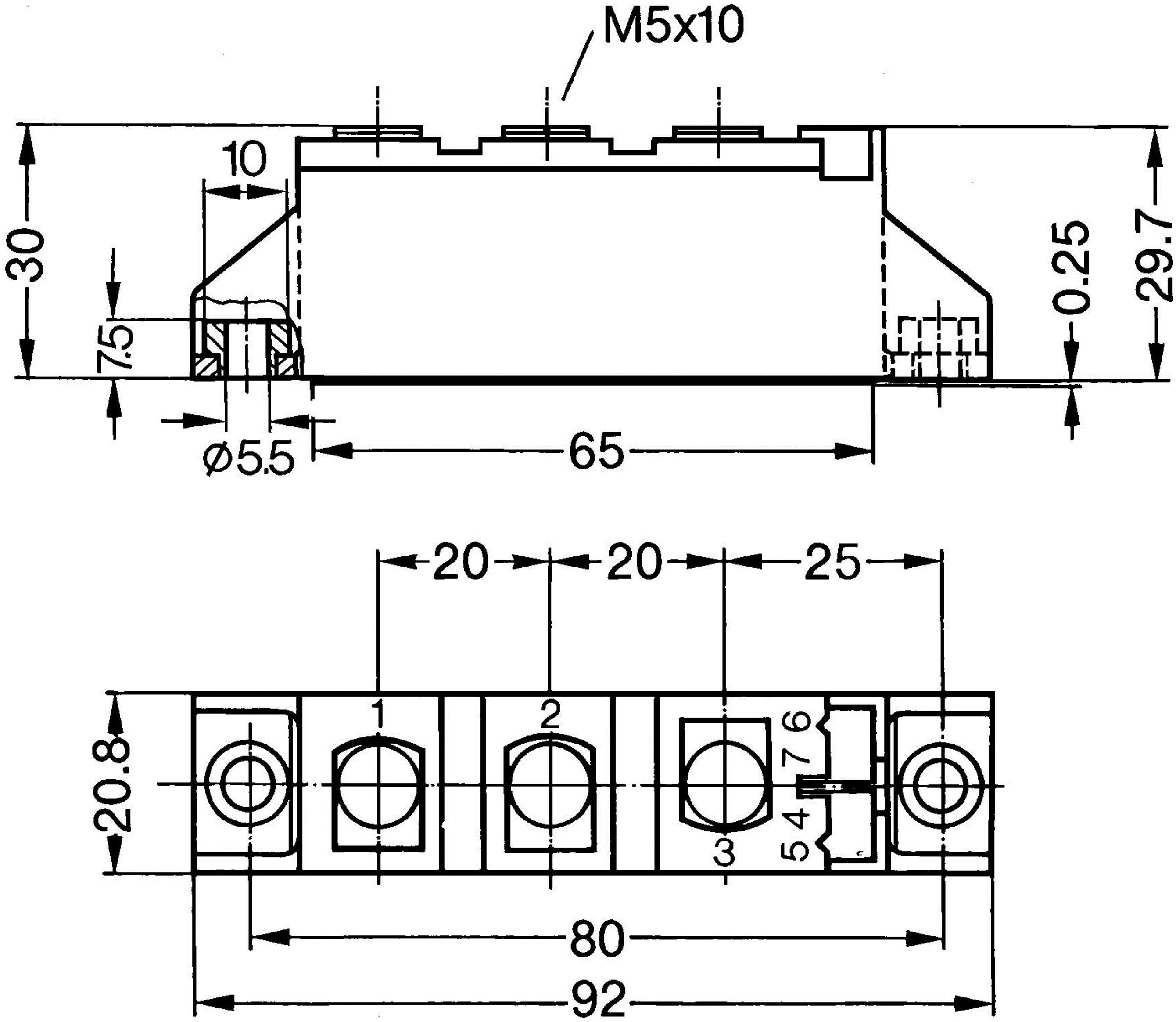
Equivalent Circuits for Simulation

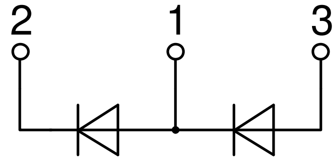
** on die level* T_{VJ} = 150 °C



		Rectifier	
$V_{0\ max}$	*threshold voltage*	0.79	V
$R_{0\ max}$	*slope resistance **	2.3	mΩ

Outlines TO-240AA





Rectifier

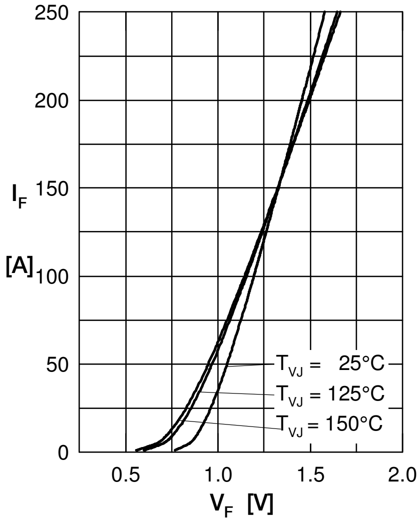


Fig. 1 Forward current versus voltage drop per diode

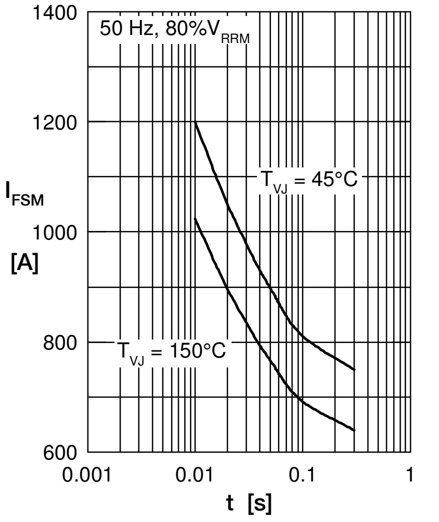


Fig. 2 Surge overload current vs. time per diode

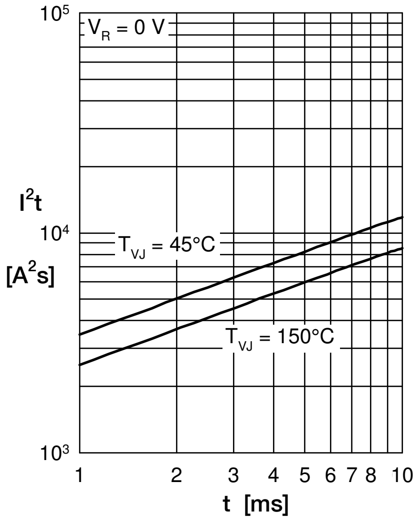


Fig. 3 I^2t versus time per diode

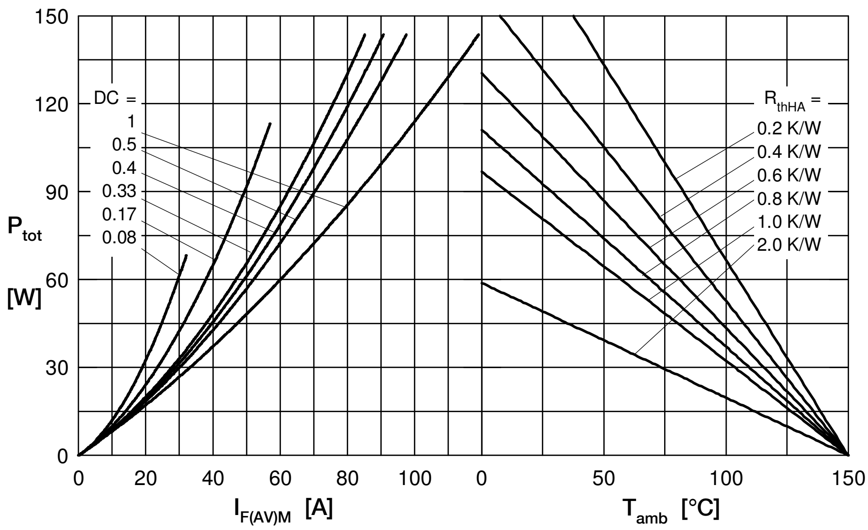


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

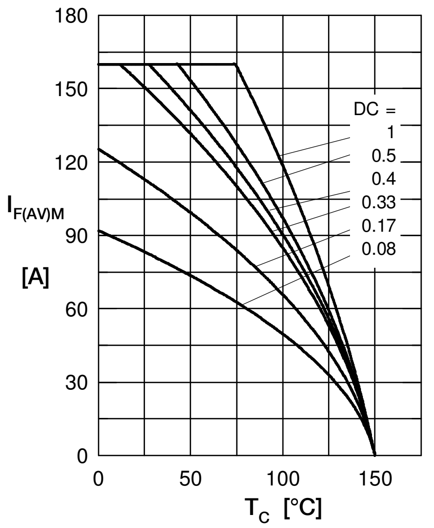


Fig. 5 Max. forward current vs. case temperature per diode

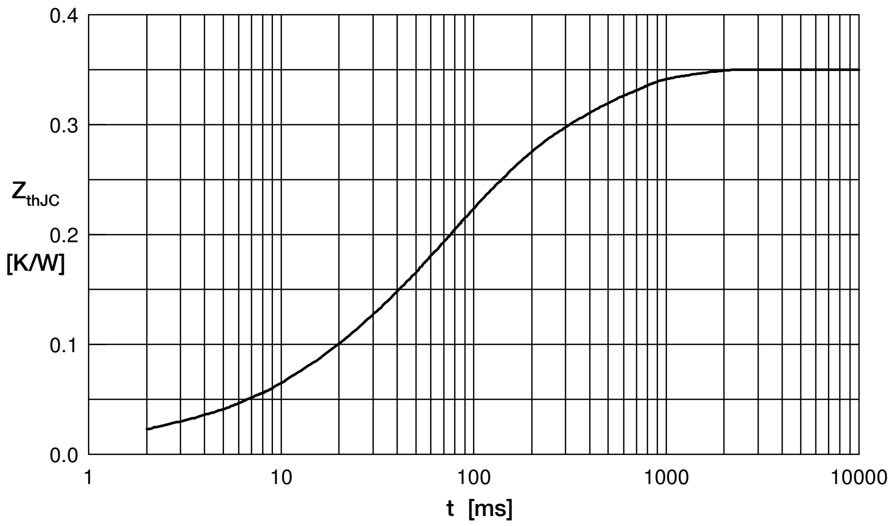


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.012	0.001
2	0.048	0.013
3	0.185	0.070
4	0.105	0.400